



HFZT

SS22---SS220

## SCHOTTKY BARRIER RECTIFIER

VOLTAGE RANGE: 20--- 200 V CURRENT: 2.0 A

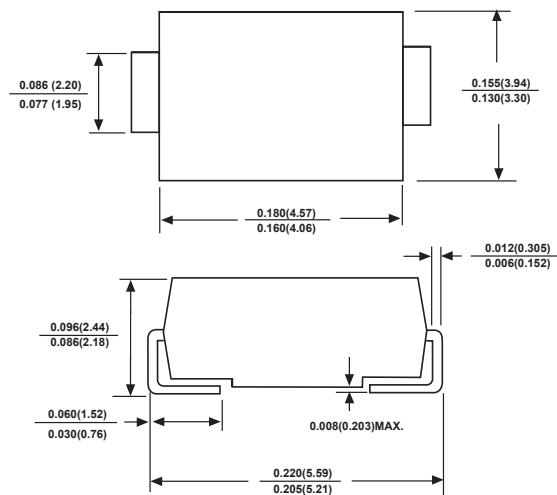
### FEATURES

- Plastic package has Underwriters Laboratory Flammability Classification 94V-O Utilizing
- Metal silicon junction ,majority carrier conduction
- Built-in strain relief
- For surface mounted applications
- Low power loss ,high efficiency,High surge capability
- High current capability ,Low forward voltage drop
- For use in low voltage ,high frequency inverters, free wheeling , and polarity protection applications
- High temperature soldering guaranteed:260 °C/10 seconds at terminals
- Component in accordance to RoHS 2002/95/Ec and WEEE 2002/96/EC

### MECHANICAL DATA

- Case: SMB molded plastic body
- Terminals:Lead solderable per MIL-STD-750,method 2026
- Polarity:Color band denotes cathode end

### SMB



Dimensions in inches and (millimeters)

### MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted) Single phase,half wave,60 Hz,resistive or inductive load.

For capacitive load,derate by 20%.

TYPE NUMBER	SYMBOL	SS22	SS23	SS24	SS25	SS26	SS28	SS210	SS215	SS220	UNITS						
Maximum recurrent peak reverse voltage	$V_{RRM}$	20	30	40	50	60	80	100	150	200	V						
Maximum RMS voltage	$V_{RMS}$	14	21	28	35	42	57	71	105	140	V						
Maximum DC blocking voltage	$V_{DC}$	20	30	40	50	60	80	100	150	200	V						
Maximum Average Forward rectified Current0.375"(9.5mm) lead length	$I_{F(AV)}$	2.0									A						
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load	$I_{FSM}$	30.0									A						
Maximum instantaneous forward voltage at 2.0 A (Note1)	$V_F$	0.55		0.75		0.85		0.90		0.95	V						
Maximum reverse current @ $T_A=25^\circ C$	$I_R$	0.2									mA						
at rated DC blocking voltage per diode @ $T_A=100^\circ C$		10.0															
Typical Thermal Resistance (Note 2)	$R_{\theta JA}$	55.0									°C/W						
Typical junction capacitance (Note 3)	$C_j$	75									pF						
Storage Temperature	$T_{STG}$	- 56 ---- + 150									°C						
Operation Junction Temperature	$T_j$	- 55 ---- + 125									°C						

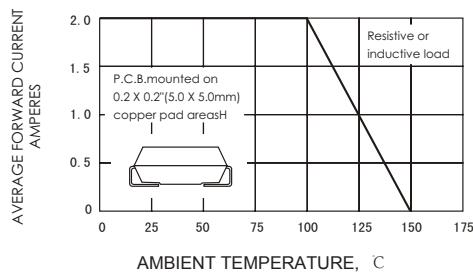
NOTE: 1.Measured at 1MHz and applied reverse voltage of 4.0V D.C.

2.P.C.B. mounted with 0.2x0.2"(5.0x5.0mm) copper pad areas

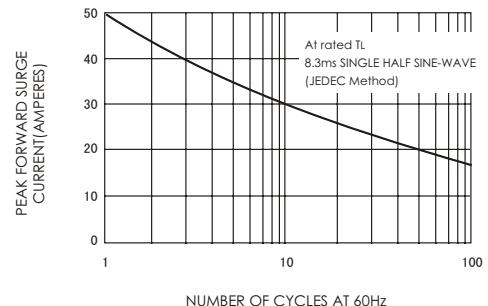


## RATINGS AND CHARACTERISTIC CURVES

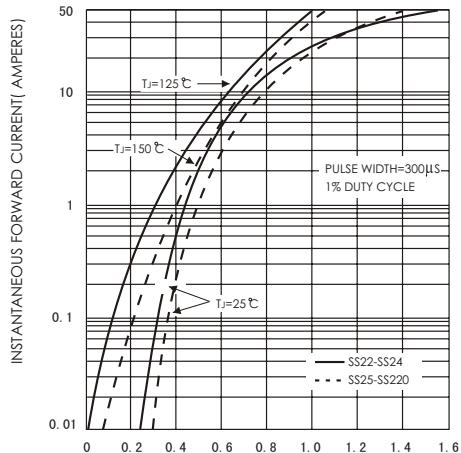
**FIG. 1- FORWARD CURRENT DERATING CURVE**



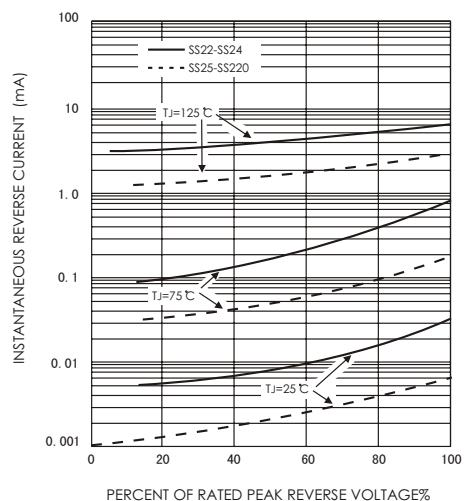
**FIG. 2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT**



**FIG. 3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS**



**FIG. 4-TYPICAL REVERSE CHARACTERISTICS**



**FIG. 5-TYPICAL JUNCTION CAPACITANCE**

